

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD550** is Designed for

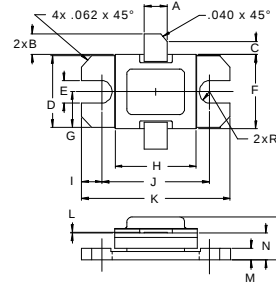
FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	40 A
V_{CC}	55 V
P_{DISS}	1350 W @ $T_C \leq 80^\circ\text{C}$
T_J	-65°C to $+250^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	0.06°C/W

PACKAGE STYLE .400 2L FLG (A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.135 / 3.43	.145 / 3.68
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.376 / 9.55	.396 / 10.06
E	.110 / 2.79	.130 / 3.30
F	.395 / 10.03	.407 / 10.34
G	.193 / 4.90	
H	.490 / 12.45	.510 / 12.95
I	.100 / 2.54	
J	.690 / 17.53	.710 / 18.03
K	.890 / 22.61	.910 / 23.11
L	.003 / 0.08	.006 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

ORDER CODE: ASI10568

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 25\text{ mA}$	65			V
BV_{CER}	$I_C = 50\text{ mA}$ $R_{BE} = 10\ \Omega$	65			V
BV_{EBO}	$I_E = 5\text{ mA}$	3.5			V
I_{CES}	$V_{CE} = 50\text{ V}$			60	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 2.0\text{ A}$	10		250	---
P_G	$V_{CC} = 50\text{ V}$ $P_{OUT} = 550\text{ W}$ $f = 1025 - 1150$	5.6			dB
η_c	MHZ	40			%